# **EECS151: Introduction to Digital Design and ICs**

# Lecture 17 – Energy, Adders

## **Bora Nikolić**

#### Brain implant bypasses the eyes to help blind users "see" images

October 20, 2021, NewAtlas - While there are already eye implants that allow the blind to see simple patterns, Spanish scientists have recently had success with a different approach. They bypassed the eyes, producing perceivable images by directly stimulating the brain's visual cortex. The experimental system incorporates a forward-facing "artificial retina" mounted on an ordinary pair of glasses worn by the user. That device detects light from the visual field in front of the glasses, and converts it to electrical signals which are transmitted to a three-dimensional matrix of 96 micro-electrodes implanted in the user's brain.





The implanted intracortical microelectrode array allowed a blind test subject to perceive letters and silhouettes of shapes

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### Review

- Wire contributes to delay, especially in modern technology
- We can use RC model to capture wire delays
- Energy becomes an increasingly important optimization goal
  - Dynamic energy
  - Static energy

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# **Dynamic Power**

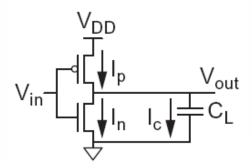
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### Charging and Discharging a Capacitor

- When the gate output rises
  - $E_C = \frac{1}{2} C_L V_{DD}^2$ Energy stored in capacitor is
  - But energy drawn from the supply is

$$E_{VDD} = \int_{0}^{\infty} I(t)V_{DD}dt = \int_{0}^{\infty} C_{L} \frac{dV}{dt} V_{DD}dt$$
$$= C_{L}V_{DD} \int_{0}^{V_{DD}} dV = C_{L}V_{DD}^{2}$$



- Half the energy from V<sub>DD</sub> is dissipated in the pMOS transistor as heat, other half stored in capacitor
- When the gate output transitions HL
  - Energy in capacitor is dumped to GND
  - Dissipated as heat in the NMOS transistor

### **Dynamic Power Reduction**

How can we limit switching power?

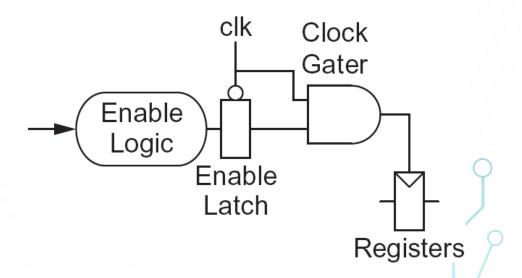
- Try to minimize:
  - Activity factor
  - Capacitance
  - Supply voltage
  - Frequency

$$P_{\text{switching}} = \alpha C V_{DD}^{2} f$$

### Reduce Activity Factor

$$P_{\text{switching}} = \alpha C V_{DD}^{2} f$$

- Clock gating
- The best way to reduce the activity is to turn off the clock to registers in inactive blocks
  - Saves clock activity (clock a = 1)
  - Eliminates all switching activity in the block
  - Requires determining if block will be used



### Reduce Capacitance

$$P_{\text{switching}} = \alpha C V_{DD}^{2} f$$

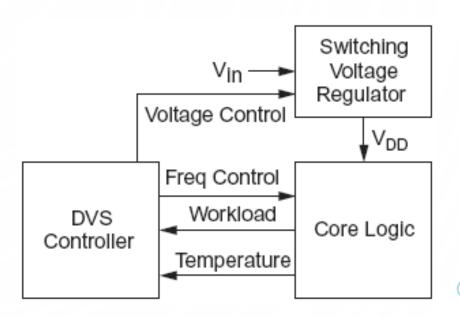
- Gate capacitance
  - Fewer stages of logic
  - Smaller gate sizes
- Wire capacitance
  - Good floorplanning to keep communicating blocks close to each other

## Reduce Voltage/Frequency

$$P_{\text{switching}} = \alpha C V_{DD}^2 f$$

 Run each block at the lowest possible voltage and frequency that meets performance requirements

- Voltage domains
  - Provide separate supplies to different blocks
- Dynamic voltage/frequency scaling
  - ullet Adjust  $V_{\text{DD}}$  and f according to workload



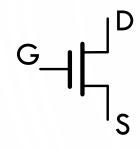


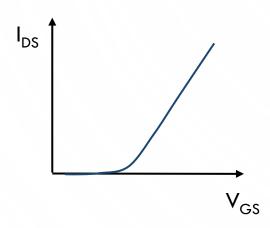
Leakage Power

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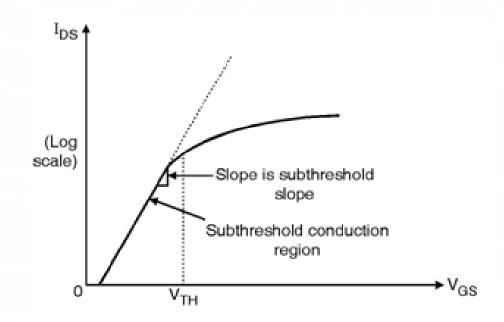
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### Subthreshold Leakage





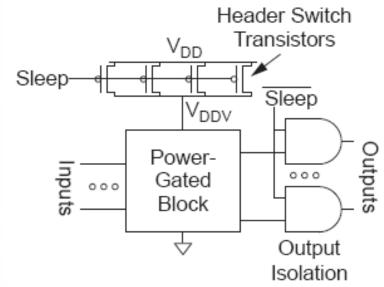
Nearly linear  $I_{DS} \sim K(V_{GS}-V_{Th})$ 



 $\rm I_{DS}\,Vs\,V_{GS}$  characteristics in log scale

### **Power Gating**

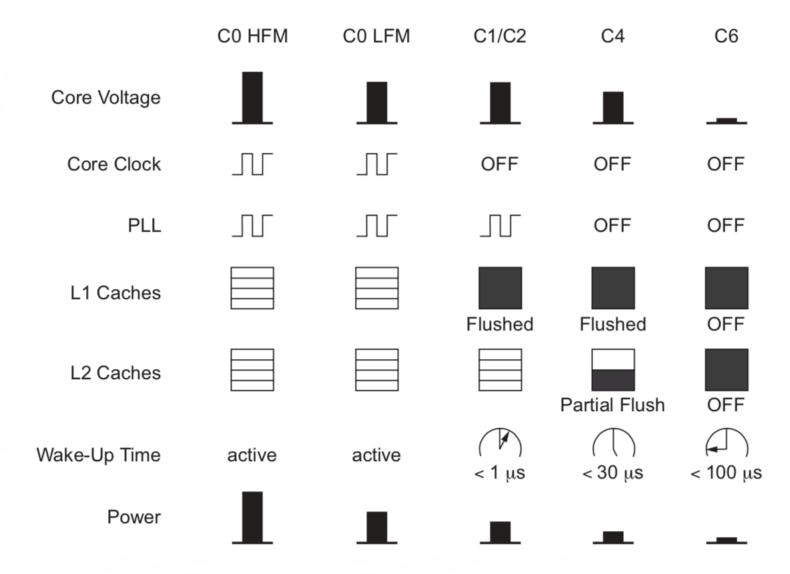
- Turn OFF power to blocks when they are idle to save leakage
  - Use virtual  $V_{DD}$   $(V_{DDV})$
  - Gate outputs to prevent invalid logic levels to next block
- Voltage drop across sleep transistor degrades performance during normal operation
  - Size the transistor wide enough to minimize impact
- Switching wide sleep transistor costs dynamic power
  - Only justified when circuit sleeps long enough



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### **Example: Power Management**

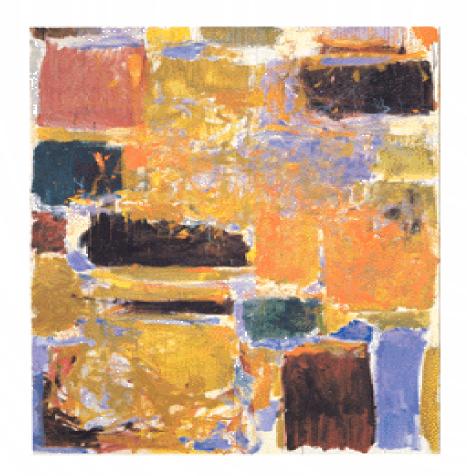
Power states



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### Administrivia

- Homework 7 due this week
  - No new homework next week
- All labs need to be checked off by this week!
- Projects (ASIC and FPGA) started
- Midterm 2 is on November 4 at 7pm
  - Review session this Wednesday at 7pm



# **Binary Adders**

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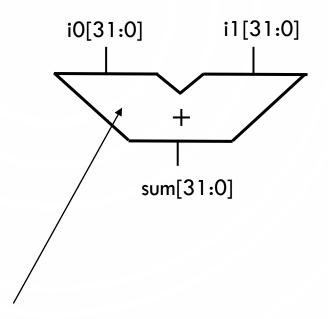
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### **Binary Adder**

### Adders

```
module add32(i0,i1,sum);
input [31:0] i0,i1;
output [31:0] sum;
assign sum = i0 + i1;
endmodule
```



What's inside?

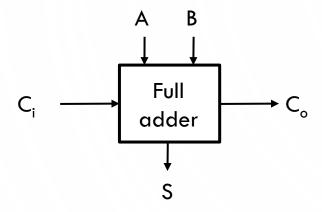
Depends on:

- Performance/power requirements
- Number of bits



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## Single-Bit Full-Adder



A	В	C <sub>in</sub>	C°	S	Carry Status
0	0	0			
0	0	1			
0	1	0			
0	1	1			
1	0	0			
1	0	1			
1	1	0			
1	1	1			

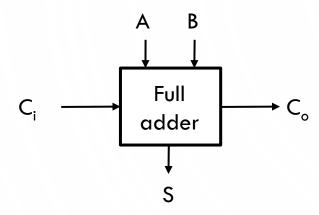
Carry status = {generate, propagate, delete}

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## Single-Bit Full Adder

### Logic equations



$$S = A \oplus B \oplus Ci$$

$$S = A \overline{B} \overline{C_i} + \overline{A} B \overline{C_i} + \overline{A} \overline{B} C_i + A B Ci$$

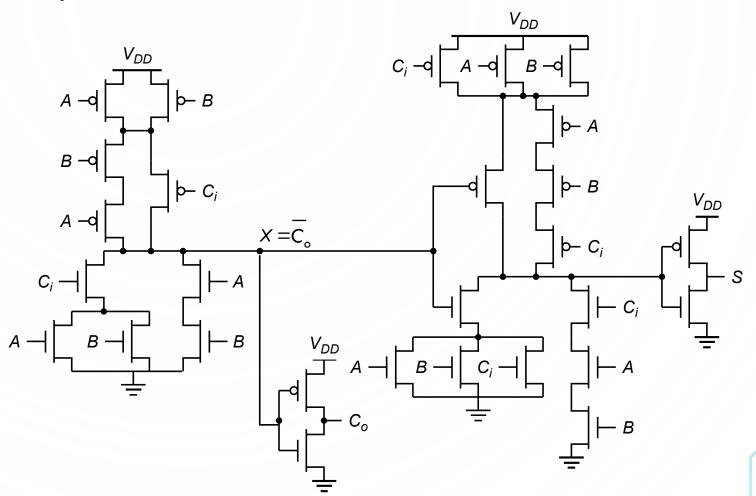
$$C_0 = A B + B Ci + A Ci$$

### Static CMOS Full Adder

Direct mapping of logic equations

$$\frac{C_o}{C_o} = \frac{A B + B Ci + A Ci}{AB + C_i(A + B)}$$

$$S = ABC_i + (A + B + C_i) \overline{C_o}$$



28 Transistors

## Express Sum and Carry as a function of P, G, D

- Define generate, propagate and delete as functions of A, B
  - Will use two at a time

Generate (G) = AB

Propagate (P) = A + B ( or A 
$$\oplus$$
 B)

Delete = A B

$$C_o = A B + B Ci + A Ci = G + P C_i$$

A	В	C <sub>in</sub>	G	Р	К	C <sub>°</sub>	S
0	0	0	0	0	1	0	0
		1				0	1
0	1	0	0	1	0	0	1
		1				1	0
1	0	0	0	1	0	0	1
		1				1	0
1	1	0	1	Х	0	1	0
		1				1	1

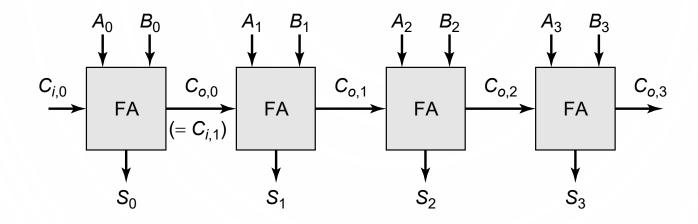
Can also derive expressions for C<sub>o</sub> based on D and P

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### The Ripple-Carry Adder

4-bit adder



#### Worst case delay linear with the number of bits

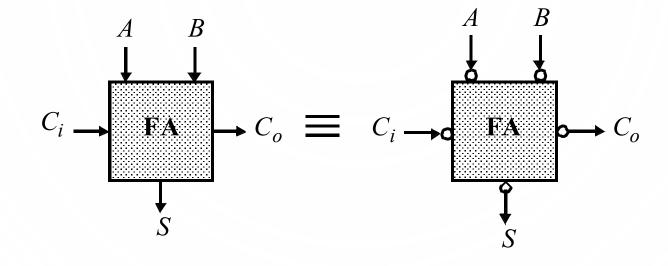
$$t_d = O(N)$$

$$t_{adder} = (N-1)t_{carry} + t_{sum}$$

Goal: Make the fastest possible carry path circuit

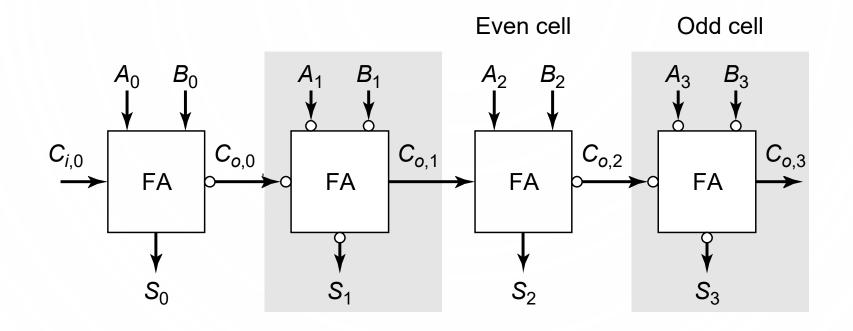
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### **Inversion Property**



$$\begin{split} \bar{S}(A,B,C_{\pmb{i}}) &= S(\bar{A},\bar{B},\overline{C}_{\pmb{i}}) \\ \overline{C}_{\pmb{o}}(A,B,C_{\pmb{i}}) &= C_{\pmb{o}}(\bar{A},\bar{B},\overline{C}_{\pmb{i}}) \end{split}$$

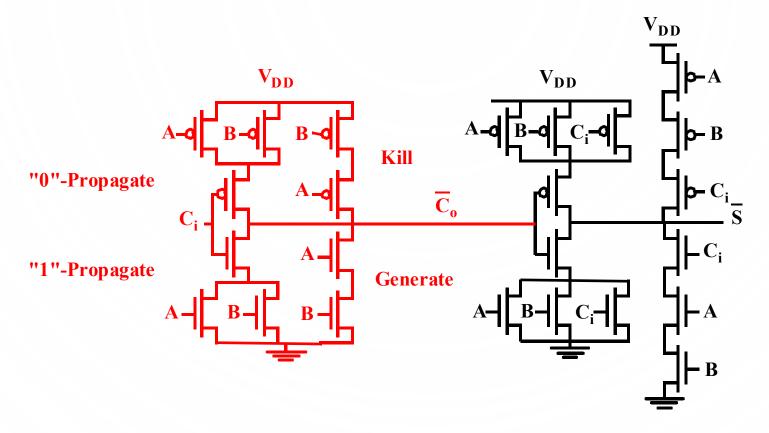
### Minimize Critical Path by Reducing Inverting Stages



**Exploit Inversion Property** 

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### A Better Structure: The Mirror Adder



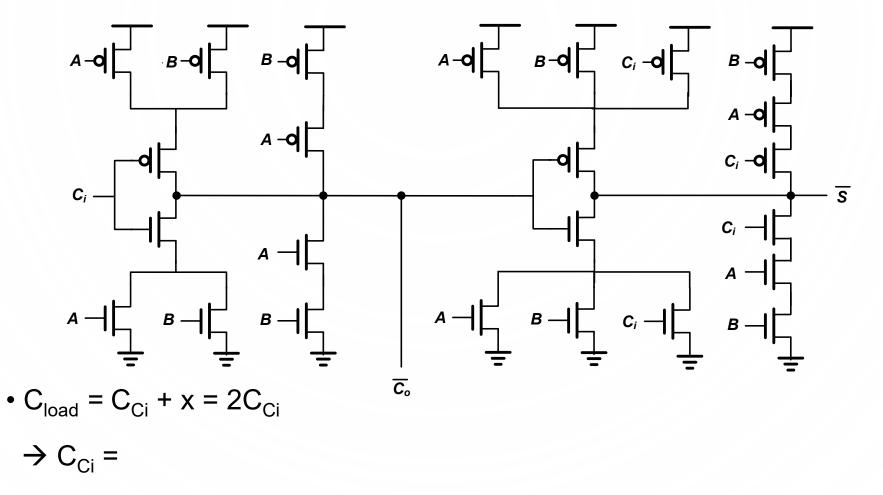
### 24 transistors

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## Sizing the Mirror Adder



Reduce size of Generate and Delete stacks to reduce diffusion loading

### The Mirror Adder

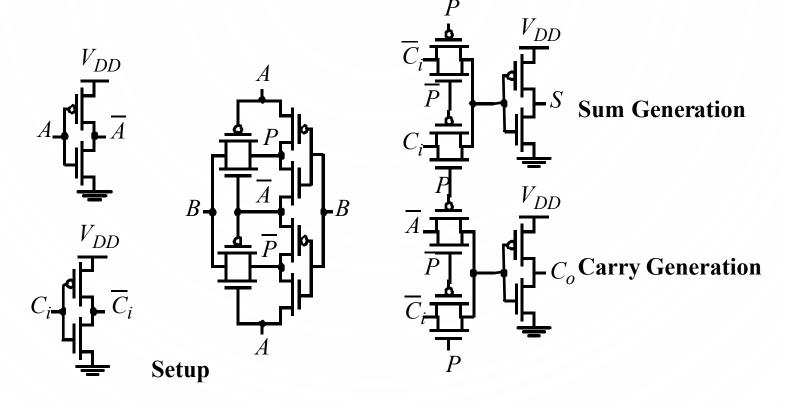
- •The NMOS and PMOS chains are completely symmetrical.

  A maximum of two series transistors in the carry-generation stack.
- •Only the transistors in the carry stage have to be optimized for optimal speed. All transistors in the sum stage can be smaller.
- •The transistors connected to C<sub>i</sub> are placed closest to the output.
- $\bullet$ Minimize the capacitance at node  $C_o$ .

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### Transmission Gate Full Adder



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# Carry Bypass Adders

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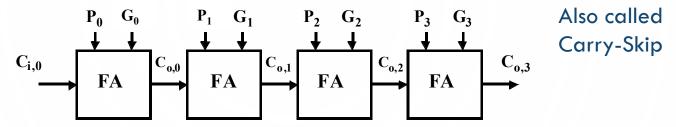
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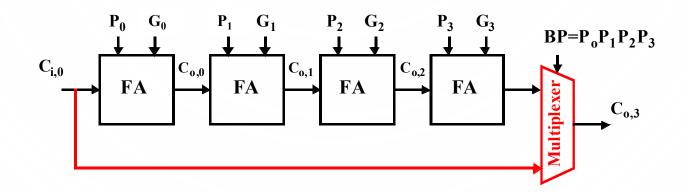
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### Carry-Bypass Adder

Also called 'carry skip'

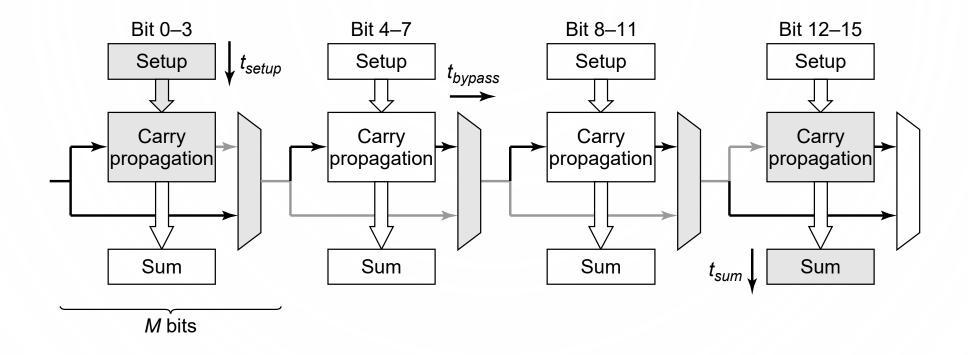




Idea: If (P0 and P1 and P2 and P3 = 1) then  $C_{o3} = C_0$ , else "kill" or "generate".

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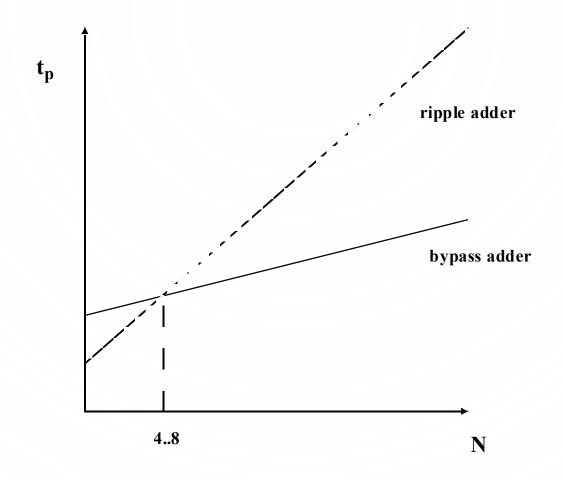
## Carry-Bypass Adder (cont.)



$$t_{adder} = t_{setup} + M_{tcarry} + (N/M-1)t_{bypass} + (M-1)t_{carry} + t_{sum}$$

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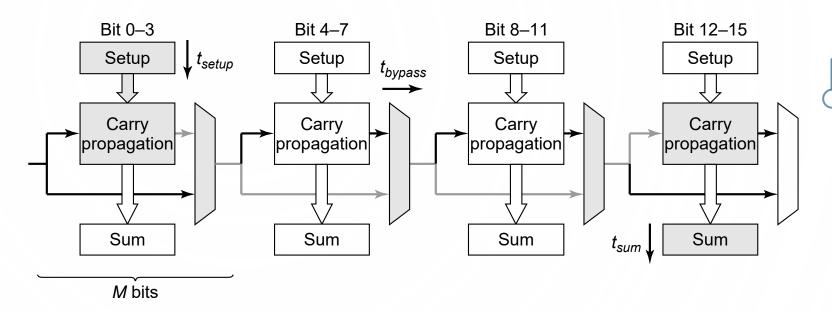
### Carry Ripple versus Carry Bypass



• Depends on technology, design constraints

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### To Design a Faster Carry-Bypass Adder



- a) Uniform groups of 4 are optimal
- b) Uniform groups >4 are optimal

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- c) Uniform groups <4 are optimal
- d) Increasing group size with higher bit position
- e) Wider groups around mid bit positions are optimal

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## Faster Carry-Bypass

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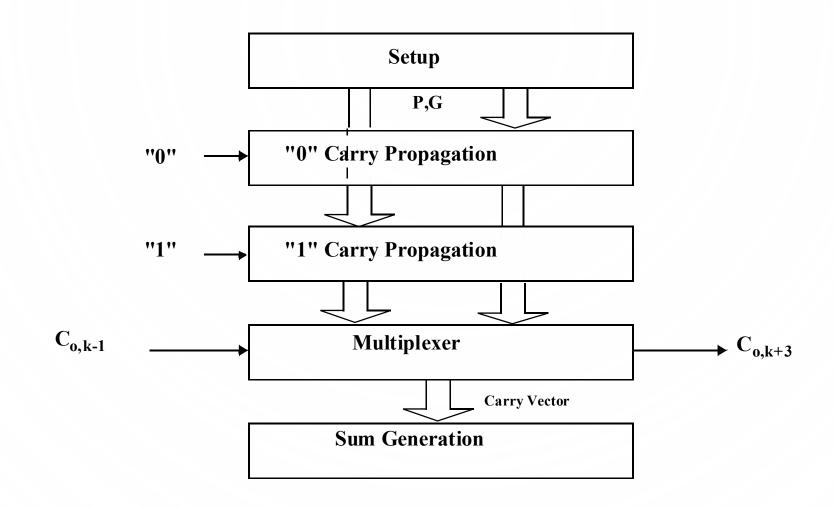
# Carry-Select Adders

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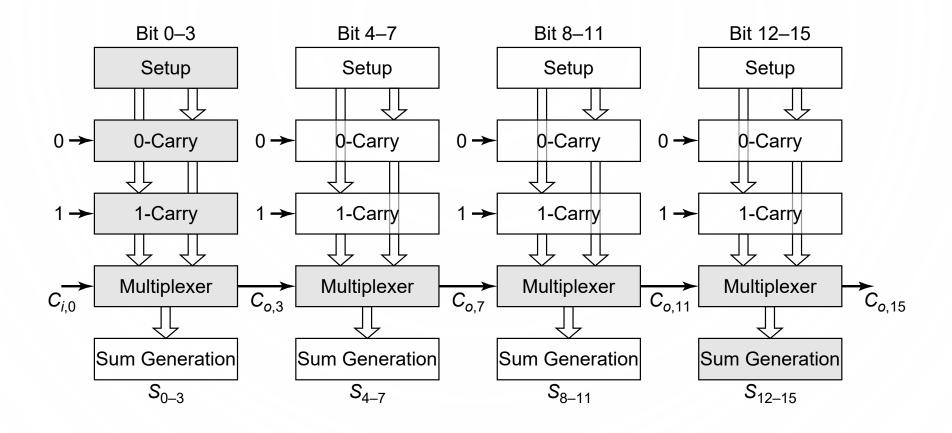
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### Carry-Select Adder



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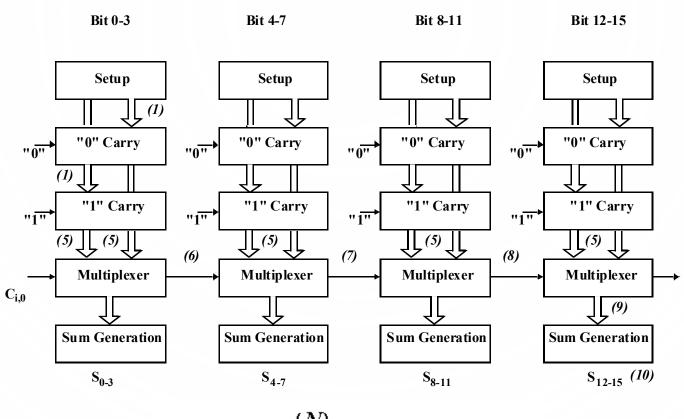
### Carry Select Adder: Critical Path



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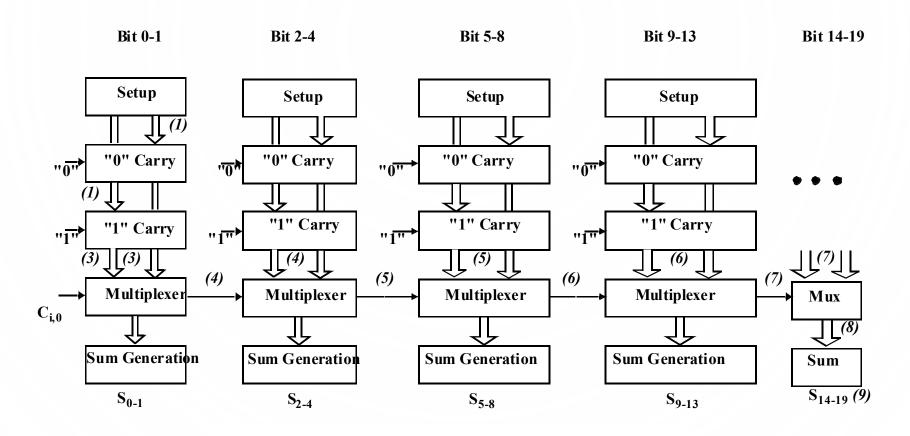
### **Linear Carry Select**



$$t_{add} = t_{setup} + \left(\frac{N}{M}\right) t_{carry} + M t_{mux} + t_{sum}$$

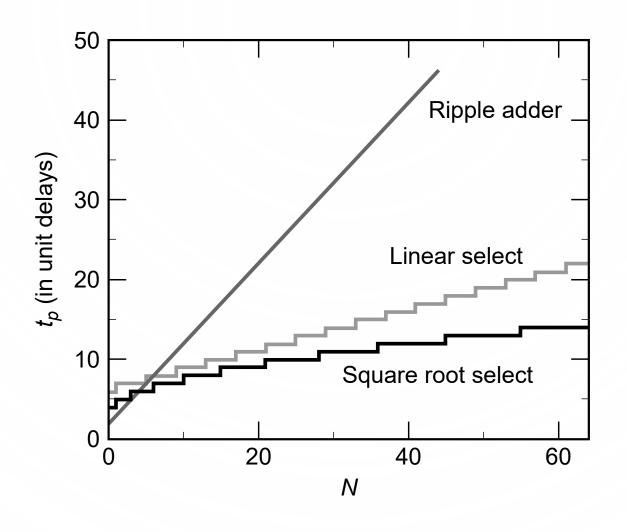
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### Square Root Carry Select



$$t_{add} = t_{setup} + P \cdot t_{carry} + (\sqrt{2N})t_{mux} + t_{sum}$$

## Adder Delays - Comparison



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### Summary

- Binary adders are a common building block of digital systems
- Carry is in the critical path
- Mirror adders cells are commonly found in libraries
- Ripple-carry adder is the least complex, lowest energy
- Carry-bypass, carry-select are usually faster than ripple-carry for bitwidths > 8

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